

NPN Silicon RF power transistor

MRF422

Description:

MRF422 is designed primarily for applications as a high-power linear amplifier from 2.0 to 30 MHz.

Features:

Specified 28 Volt, 30 MHz Characteristics
 Output Power = 150 W (PEP), Minimum Gain = 10 dB, Efficiency = 40%
 Intermodulation Distortion @ 150 W (PEP) , IMD = -30 dB (Min)

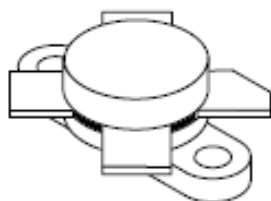
Maximum Ratings at TU = 25

Symbol	Test Conditions	Characteristics		Units
BVCEs	IC=30 mA	Max.	65	V
BVCEO	IC=60 mA	Max.	35	V
BVEBO	IE=20 mA	Max.	4	V
IC		Max.	20	A
Ptot		Max.	290	W
TSTG		Min.	-65	
		Max.	150	
TjM		Max.	200	

Characteristics at TU = 25 (VCC =28V f=30 MHz)

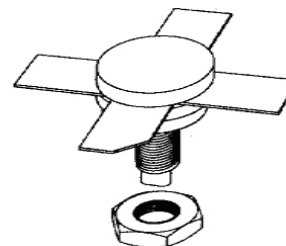
Symbol	Test Conditions	Characteristics		Units
Pout		Typ.	150*	W
GP		Typ.	12	dB
		Typ.	40	%
hFE	IC = 5A VCE =10V	Typ.	50	
VCEsat	IC = 8A IB =1.6A	Max.	2	V
ICES	VCE =36V	Max.	20	mA
CCBO	VCB =28V	Typ.	450	pF
d3		Max.	< -30	dB

Drawings:



CASE211-11

or



SOT121